





**FZT589** 

### 30V PNP MEDIUM POWER TRANSISTOR IN SOT223

### **Features**

- BV<sub>CEO</sub> > -30V
- I<sub>C</sub> = -1A High Continuous Current
- Excellent hFE Characteristics up to -2A
- Low Saturation Voltage V<sub>CE(sat)</sub> < -0.35V @ -1A</li>
- Complementary NPN Type: FZT489
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

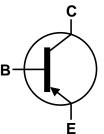
### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
   Solderable per MIL-STD-202, Method 208(€3)
- Weight: 0.112 grams (Approximate)

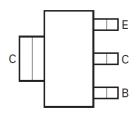




Top View



Device Symbol



Top View Pin-Out

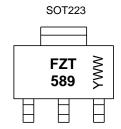
## **Ordering Information** (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT589TA	AEC-Q101	FZT589	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



FZT 589 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)





**FZT589** 

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I <sub>CM</sub>	-2	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D.	2	W
Power Dissipation	(Note 6)		3	W
Thermal Resistance, Junction to Ambient	(Note 5)	В	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	− R <sub>θJA</sub> −	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7	$R_{\theta JL}$	19.4	°C/W	
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

## ESD Ratings (Note 8)

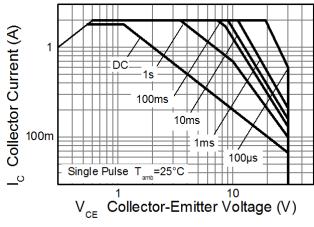
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

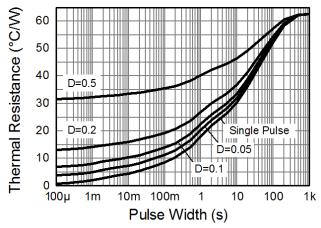
- 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under 5. For a device mounted with the collector lead on 25mm x 25mm x02 copper that is on a single-side still air conditions whilst operating in a steady-state.
  6. Same as Note 5, except the device is mounted on 50mm x 50mm single sided 2oz weight copper.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



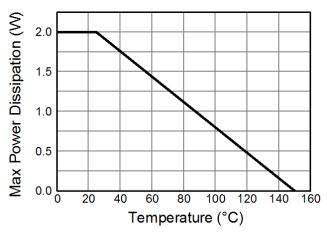
## **Thermal Characteristics and Derating Information**



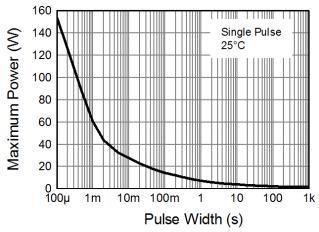
# **Safe Operating Area**



**Transient Thermal Impedance** 



# **Derating Curve**



**Pulse Power Dissipation** 





**FZT589** 

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

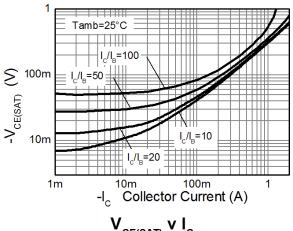
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-30	_	-	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	_	-100	nA	$V_{CB} = -30V$
Collector Emitter Cut-Off Current	I <sub>CES</sub>	-	_	-100	nA	$V_{CES} = -30V$
Emitter Cut-Off Current	I <sub>EBO</sub>	-	_	-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	-	_	-0.35	V	$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation voltage (Note 9)		_	_	-0.65		$I_C = -2A$ , $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	_	-1.2	V	$I_C = -1A$ , $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	_	-1.1	V	$I_C = -1A$ , $V_{CE} = -2V$
		100	_	_	-	$I_C = -1mA$ , $V_{CE} = -2V$
DC Current Transfer Static Ratio (Note 9)	h <sub>FE</sub>	100	_	300		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
De Guitent Transier Static Natio (Note 9)		80	_	_		$I_C = -1A$ , $V_{CE} = -2V$
		40	_	-		$I_C = -2A$ , $V_{CE} = -2V$
Transitional Frequency (Note 9)	f⊤	100	-	-	MHz	$V_{CE} = -5V, I_{C} = -100mA$ f = 100MHz
Output Capacitance (Note 9)	$C_{obo}$	-	_	15	pF	$V_{CB} = -10V. f = 1MHz$
Switching Times	t <sub>on</sub>		50	_	ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V}$
Cintorning Finnes	t <sub>off</sub>		300		110	$I_{B1} = I_{B2} = -50 \text{mA}$

Note:

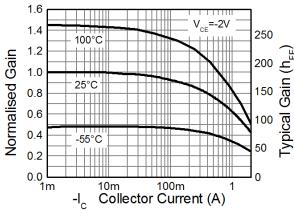
9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



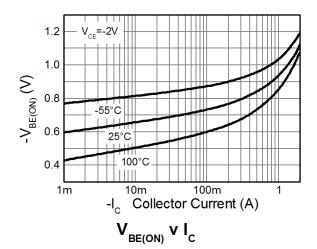
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

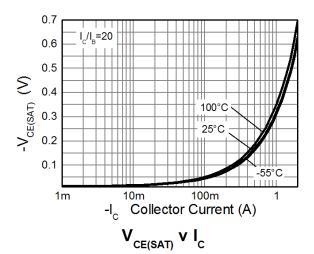


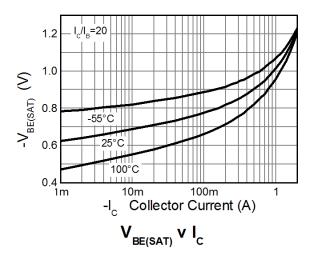




 $\mathbf{h}_{\mathrm{FE}} \ \mathbf{v} \ \mathbf{I}_{\mathrm{C}}$ 



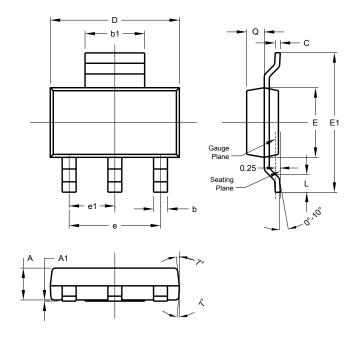






## **Package Outline Dimensions**

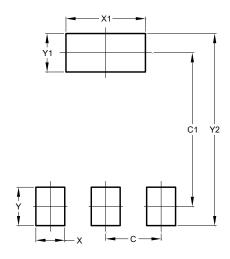
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	_	_	4.60			
e1	_	_	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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